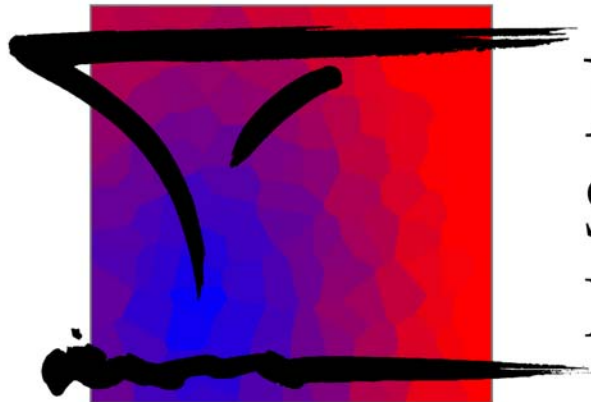


# Divergence of electron and lattice temperatures in nanometer scale contacts and structures.

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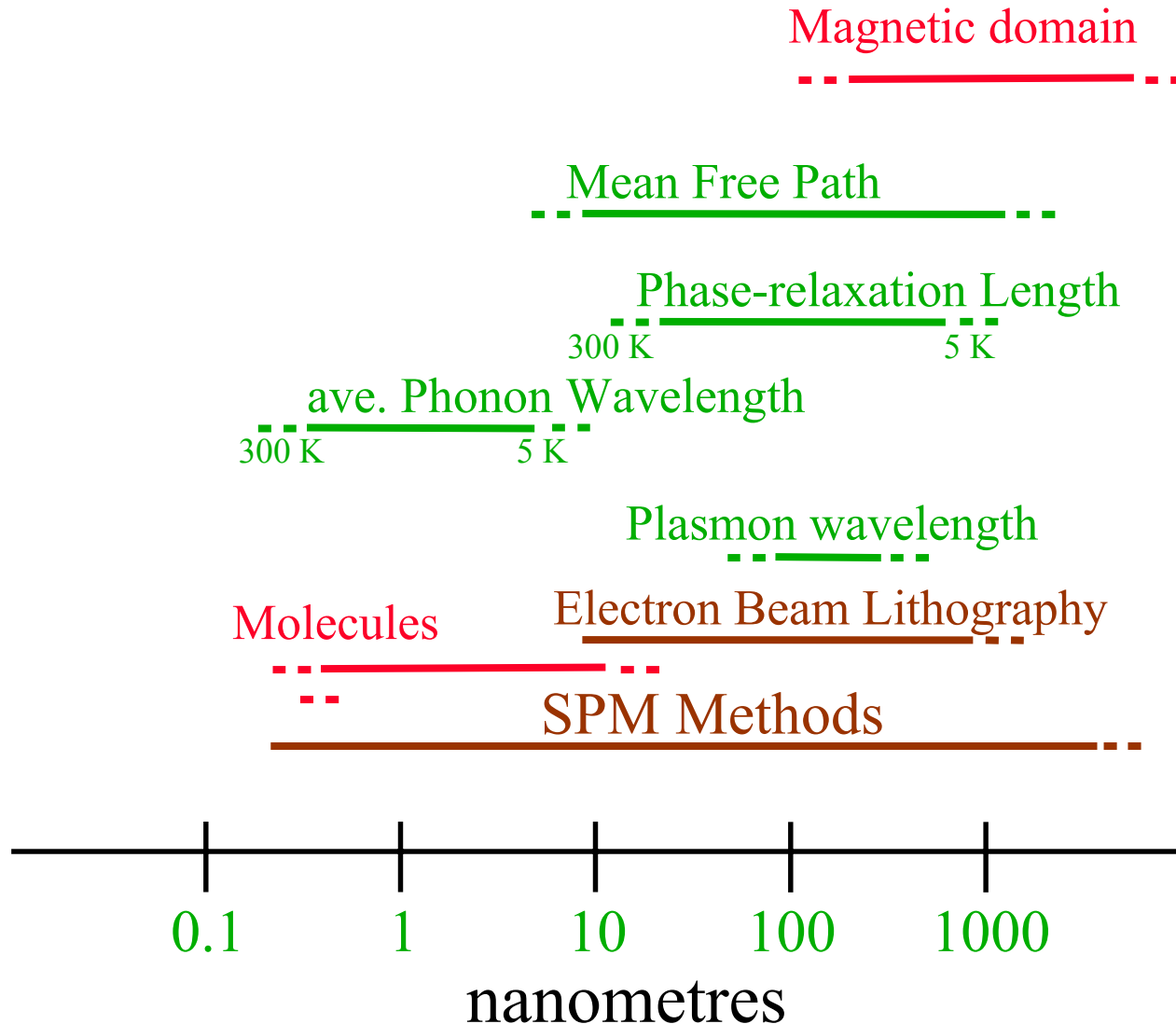


NANOSCALE  
SCIENCE  
LABORATORY

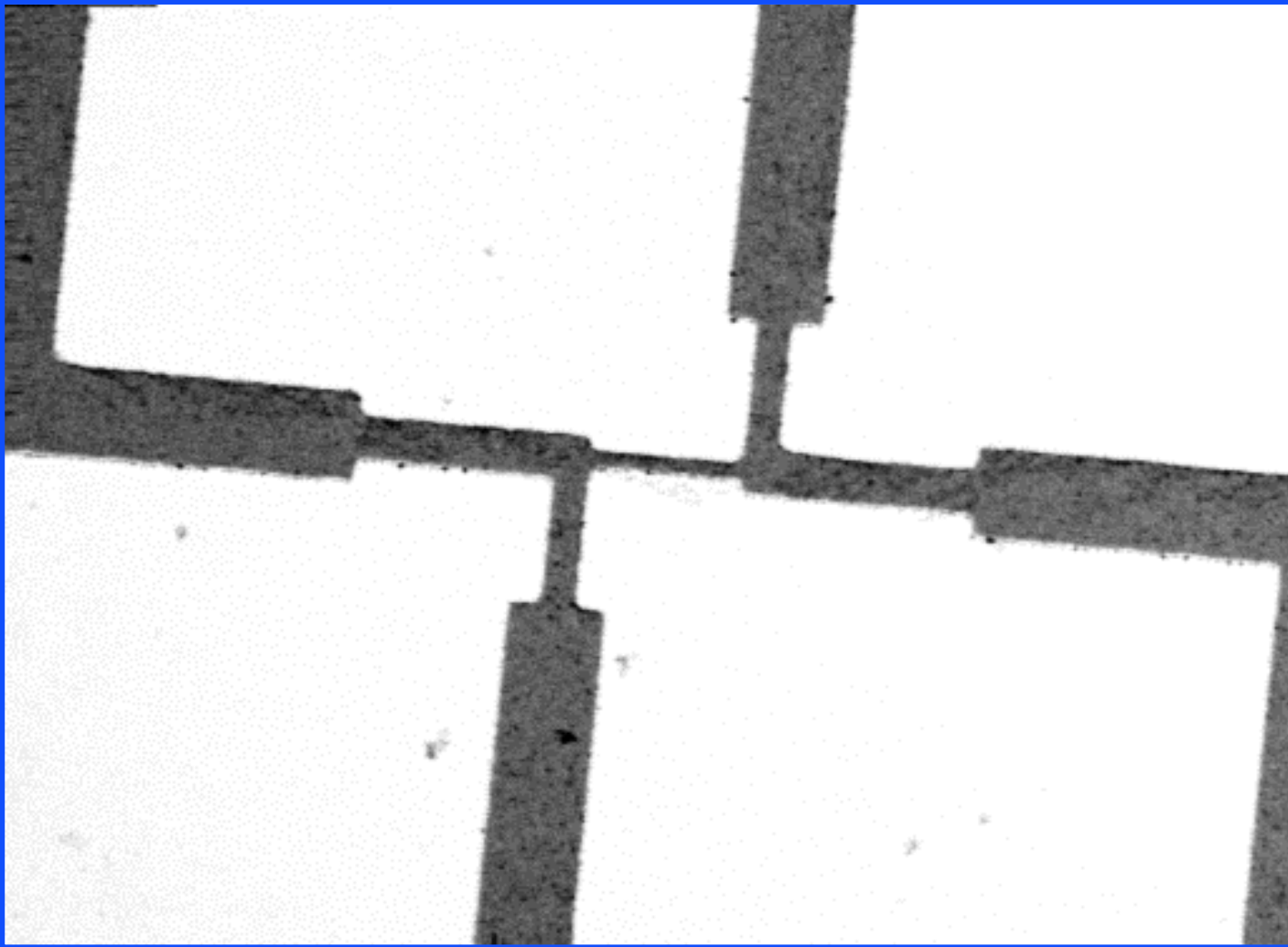
# Overview

- ⊗ **Length scales**
- ⊗ **Thermal effects in metallic nanowires**
- ⊗ **Heating in metallic point contacts**

# Length scales

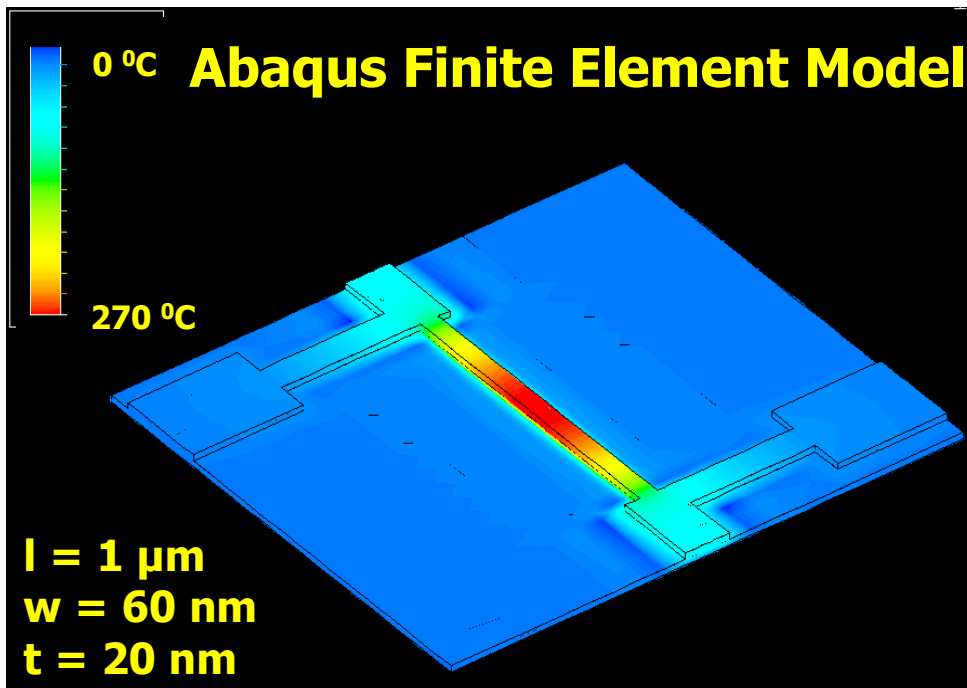


# Metallic nanowires



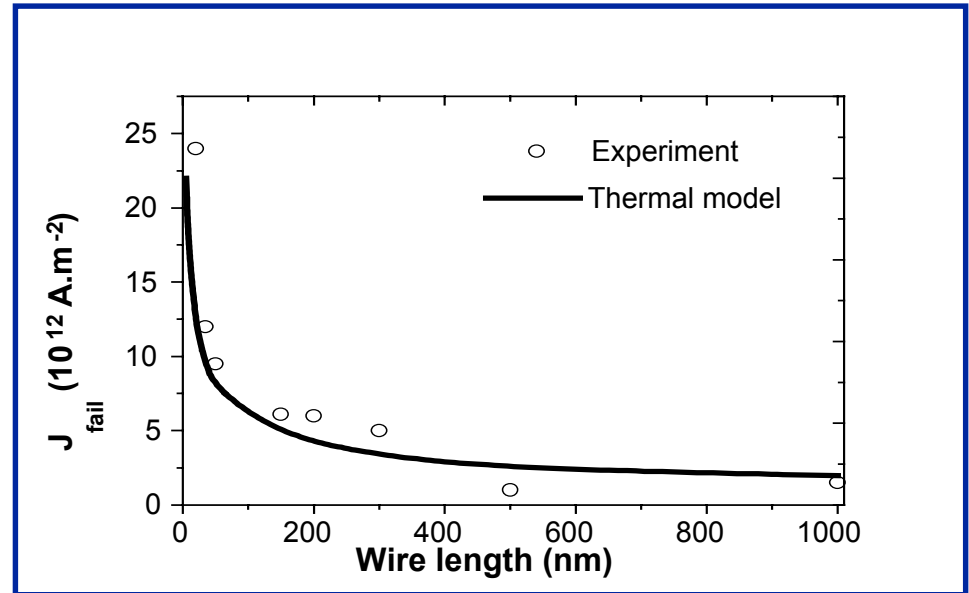
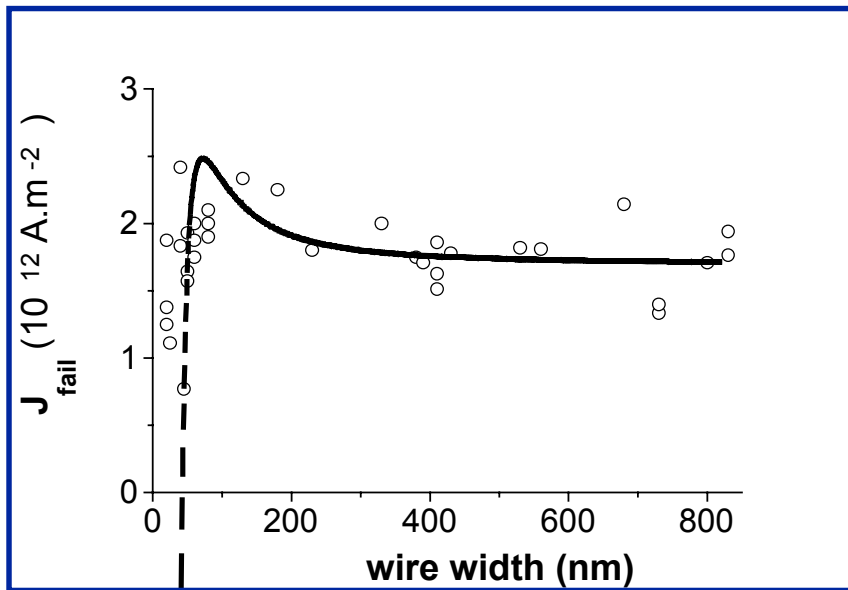
# Failure mechanisms in Nanowires (width < 100 nm):

- current - induced thermal stress
- microstructure: polycrystalline/bamboo + thermal stress = restructuring
- local electric fields, high resistivity spots, can lead to locally enhanced electromigration



- The temperature of nanowires at high current densities ( $10^{12} \text{ A.m}^{-2}$ ) is expected to reach  $>200 \text{ }^{\circ}\text{C}$

# Dependence of dimensions on failure of current-stressed nanowires



- 1  $\mu\text{m}$  long wires
- 50 nm wide wires
- Peak in  $J_{fail}$  for width  $\sim 100$  nm may be due to suppressed electron-phonon scattering

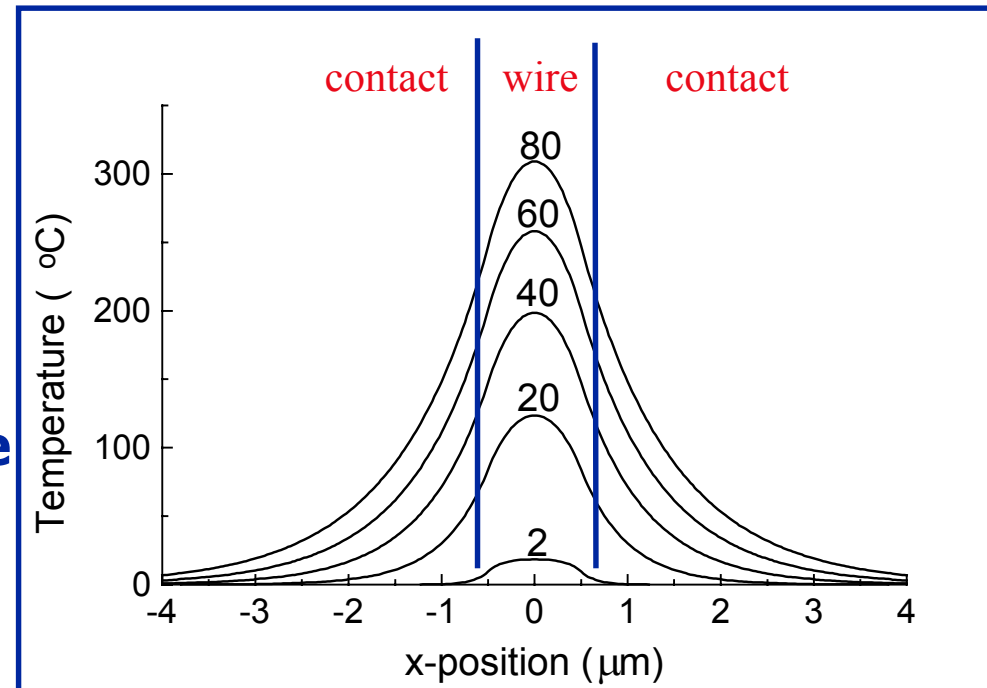
# Heating of current-stressed nanowires

- **Thermal model: solve Poisson's equation analytically:**

$$\nabla^2 T - m^2 T + \frac{Q}{k} = 0$$

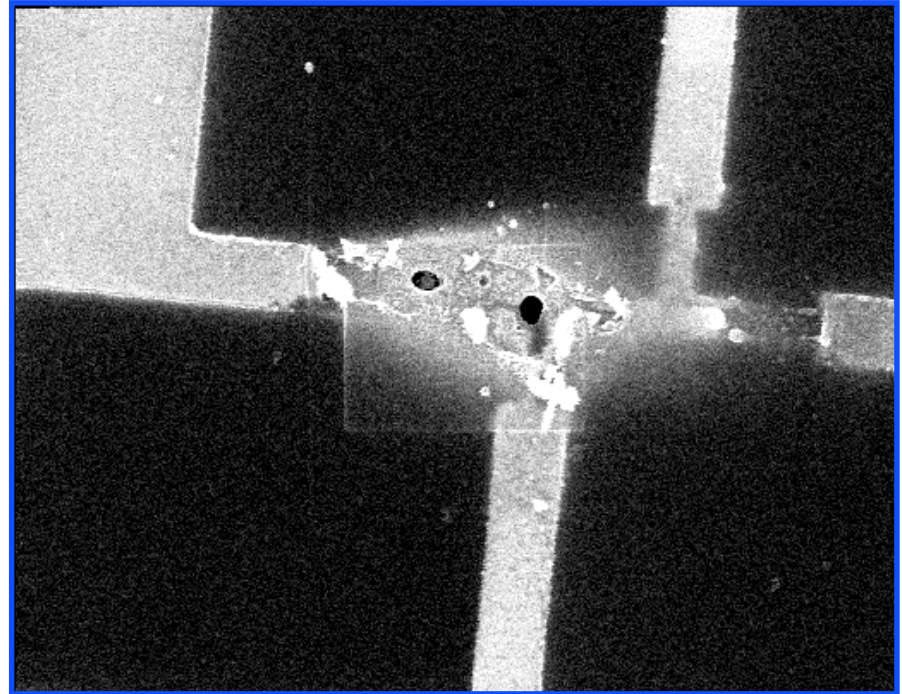
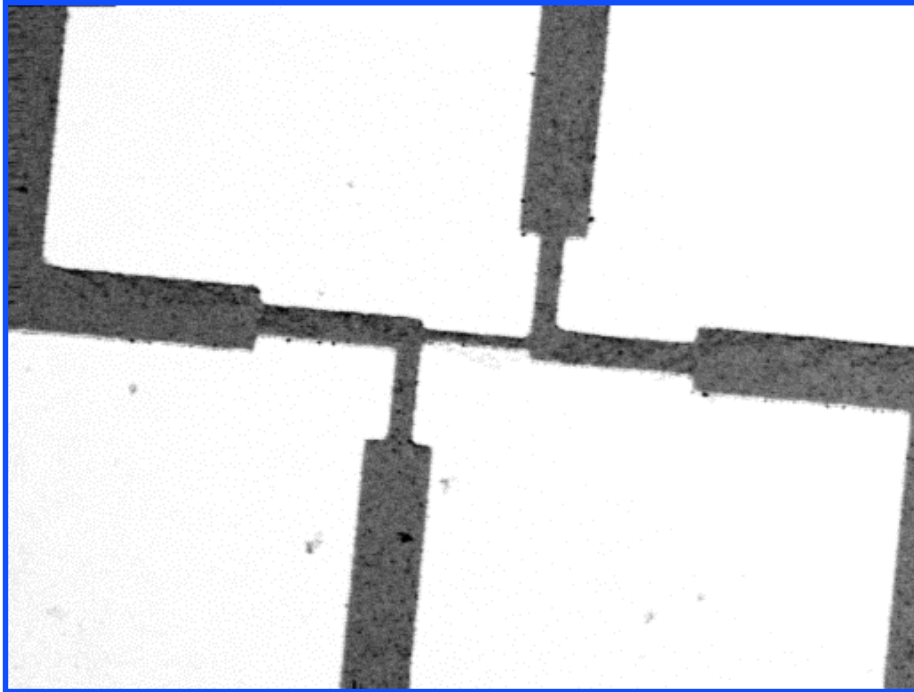
heat loss      heat generation

**Temperature in 1  $\mu\text{m}$  long wire for various substrate oxide thicknesses ,  $J=2*10^{12} \text{ A.m}^{-2}$  :**



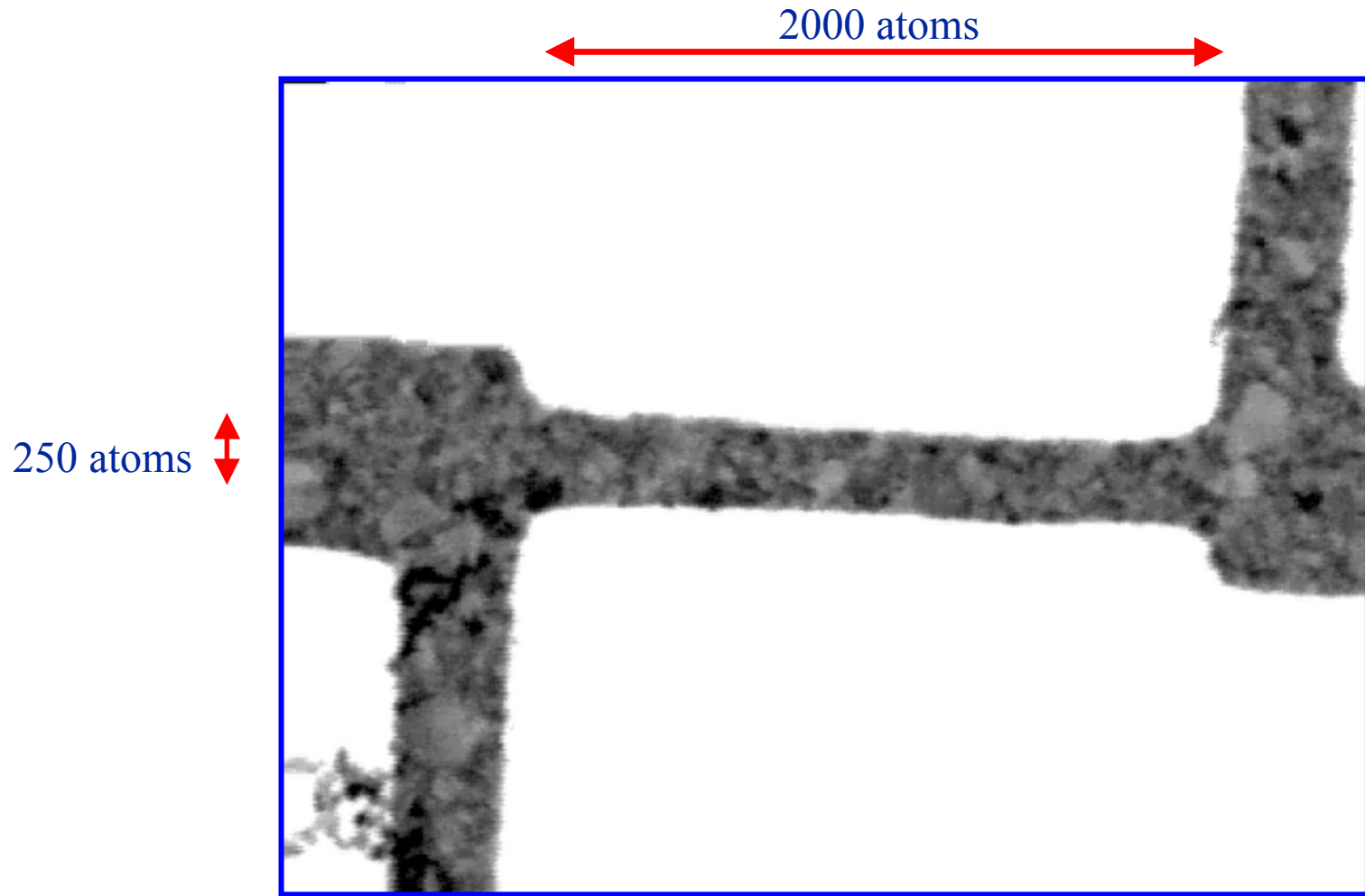
- **No explicit width dependence**
- **exponential length dependence**
- **1/(oxide thickness) dependence**
- **Temperature peaked at centre**

# Metallic wires at the nanometre scale

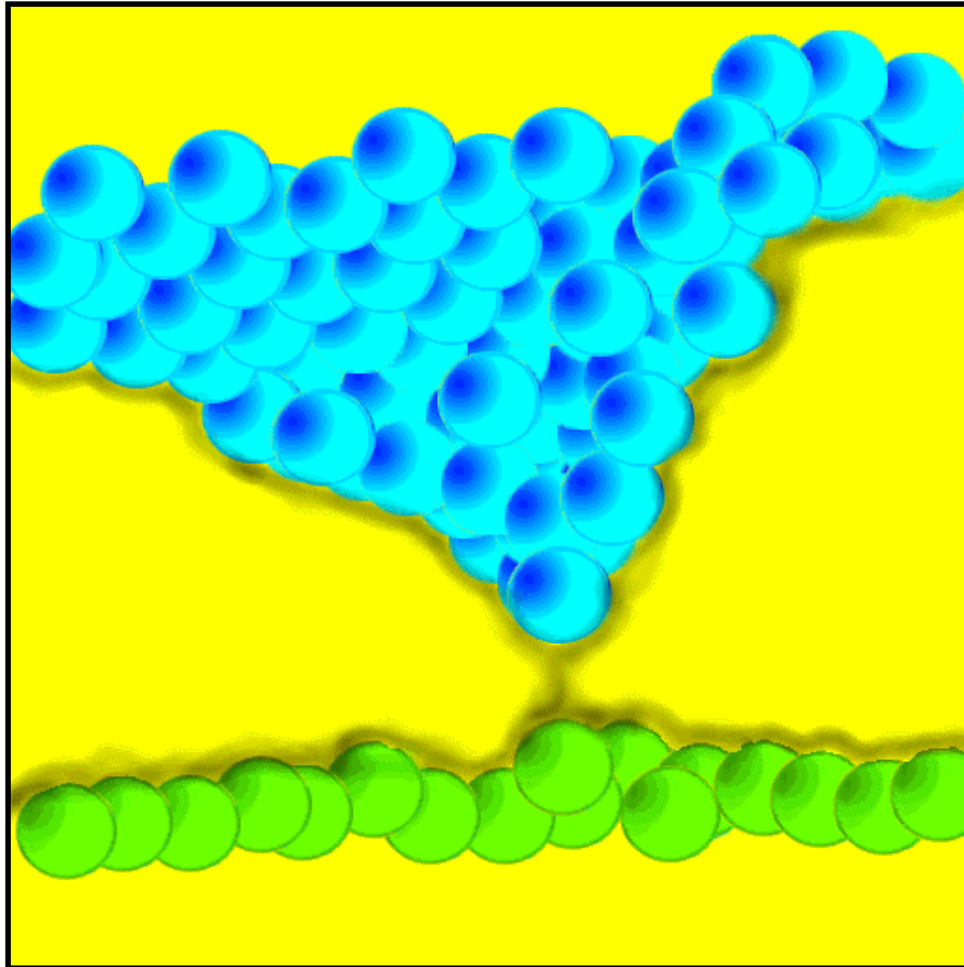




# Electrical wiring at the nanometre scale



# Point contacts in the scanning tunnelling microscope



- **Equations of heat transfer:**

$$\frac{\partial}{\partial t}(C_{el}T_{el}) = \nabla \cdot (K_{el} \nabla T_{el}) - \beta(T_{el} - T) + Q$$

$$\frac{\partial}{\partial t}(CT) = \nabla \cdot (K \nabla T) - \beta(T_{el} - T)$$

**C is heat capacity, T is absolute temperature, K is thermal conductivity, Q is power input per unit volume,  $\beta$  is a coefficient of heat transfer, "el" subscript refers to electrons.**

- **At steady state,**

$$0 = \nabla \cdot (K_{el} \nabla T_{el}) - \beta'(T_{el} - T) + IV / \text{volume}$$

(LARGE)

(SMALL)

(LARGE)

$$0 = \nabla \cdot (K \nabla T) - \beta'(T_{el} - T)$$

(SMALL)

(SMALL)

- **picture of heat transfer:**

**electrons gain energy in contact; travel away from contact; then lose energy to lattice**

- **Spontaneous photon emission should occur from high temperature electrons with a spectrum**

$$W(\nu) \sim \exp\left(\frac{-h\nu}{kT_{\text{el}}}\right)$$

**Tomchuk and Fedorovich showed**  $(kT_{\text{el}})^2 = (kT)^2 + \alpha IV$   
**comparing energy losses from electrons to the lattice.**

**( $\alpha$  is an empirical constant)**

**For**  $T_{\text{el}} \gg T$  **, this reduces to**  $kT_{\text{el}} = \sqrt{\alpha IV}$

**so**  $W(\nu) \sim \exp\left(\frac{-h\nu}{\sqrt{\alpha IV}}\right)$

- **Either look at spectrum (variation of photon emission with wavelength, keeping power input constant)**  
**→  $\alpha$  → electron temperature,  $T_{el}$**
- **Or look at variation of photon emission with power input (=IV), keeping wavelength constant**  
**—i.e. look at narrow range of wavelengths**

$$\ln(W) = \frac{-h\nu}{\sqrt{\alpha IV}} + \text{constant}$$

- **keep  $h\nu$  constant and vary IV. Slope of  $\ln(W)$  vs.  $1/\sqrt{IV}$  has a slope  $\frac{h\nu}{\sqrt{\alpha}}$ , so determine  $\alpha$ .**

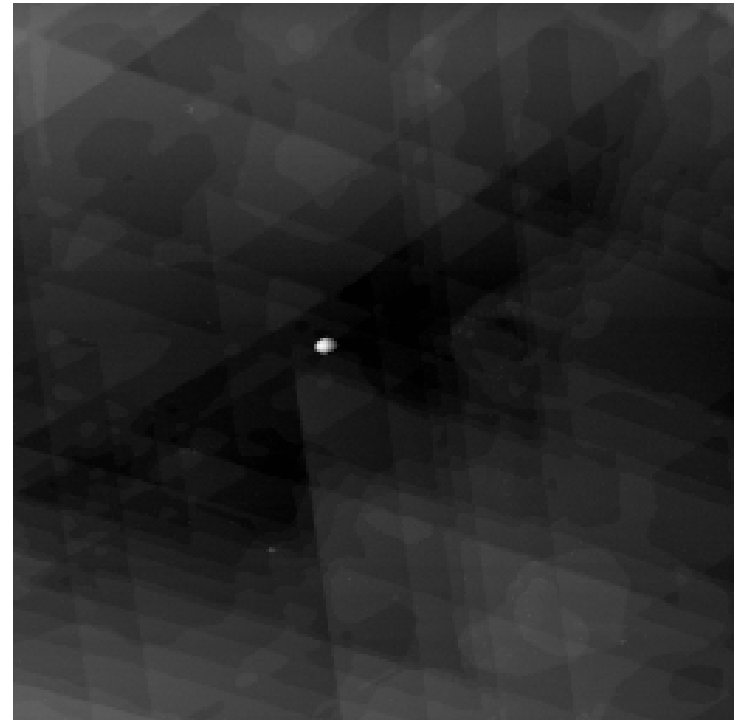
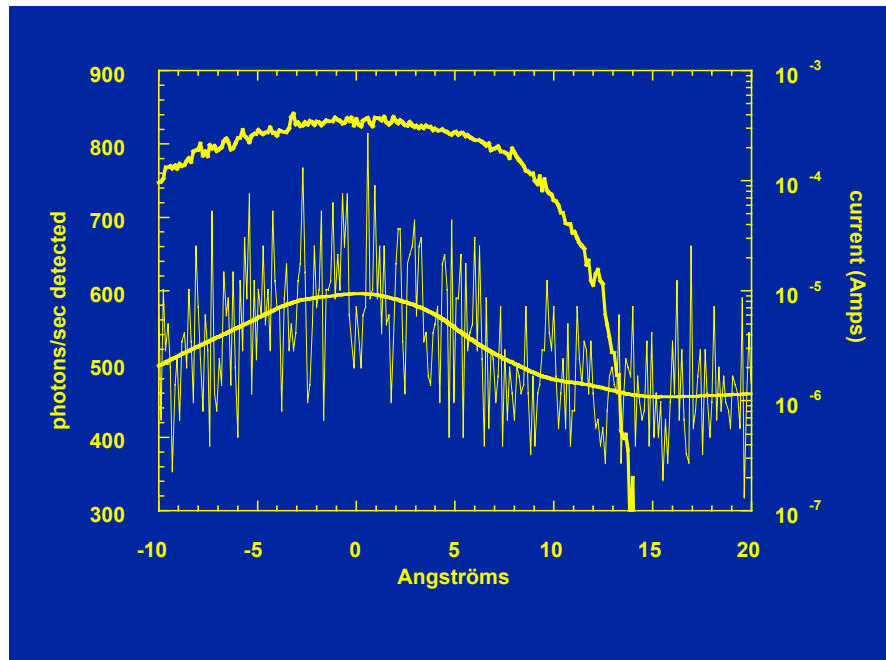
**Then  $kT_{el} = \sqrt{\alpha IV}$ , so determine electron temperature**

# Experiments

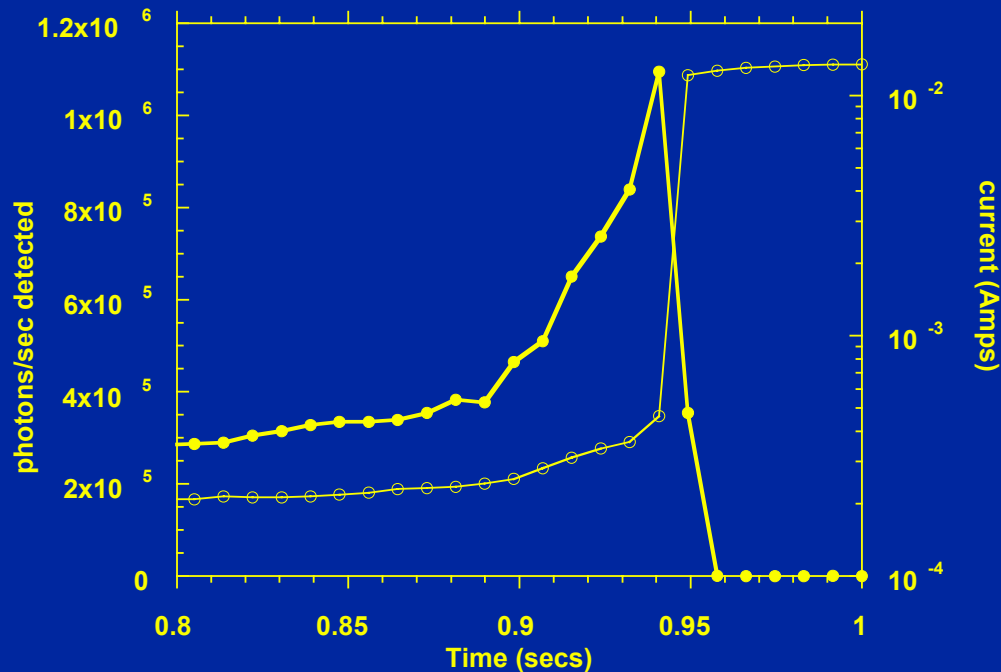
- UHV-STM operating at  $<10^{-10}$  mbar, with light collection and photomultiplier detection.  
Combined detection efficiency 1.5%
- Apply 1.5V to contact – see light emission

1.5V bias, W tip, Au sample. Inserted 10Å  
from tunneling then retracted 30Å

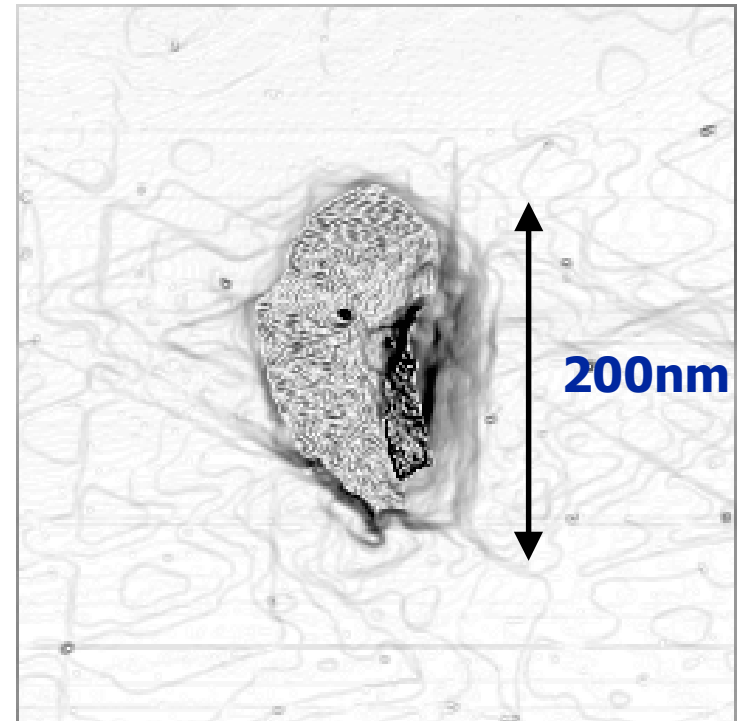
STM image after contact (5000Å x 110Å)



- **Increase contact size:**  
more light emission and contact 'melts'
- **As the contact size increases, photon emission first increases, then decreases in non-ballistic regime.**
- **Crater size matches critical L – bulk phonons**

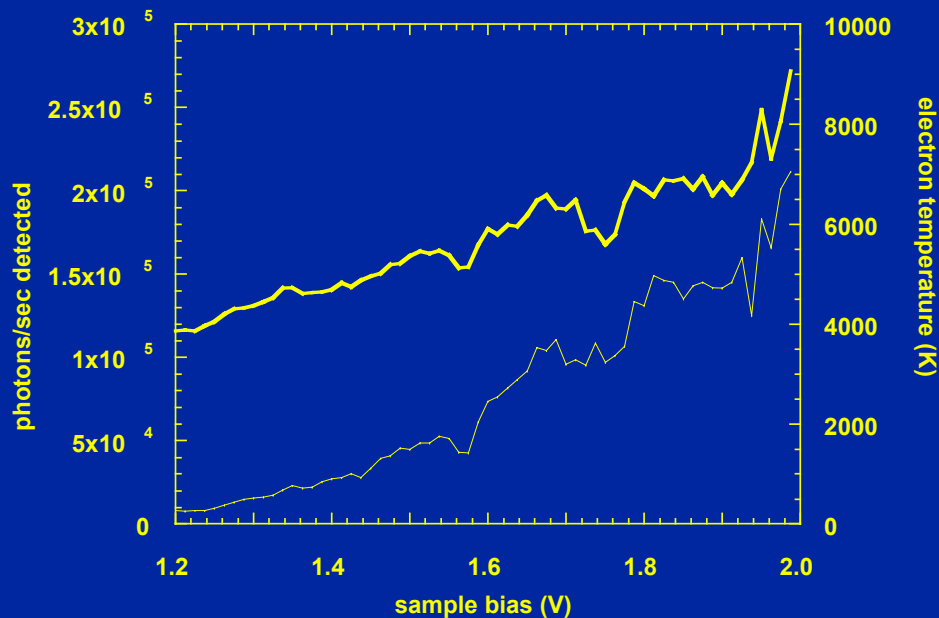
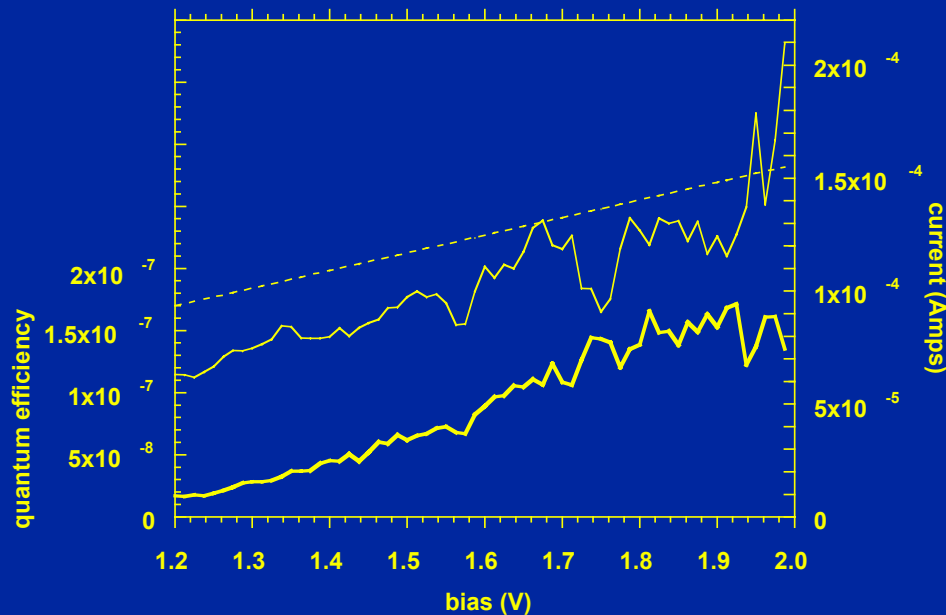


STM image of Au surface  
after contact was made



**Photons counted over the range  
-1.7–2.5eV for a varying sample  
voltage with a single atom contact**

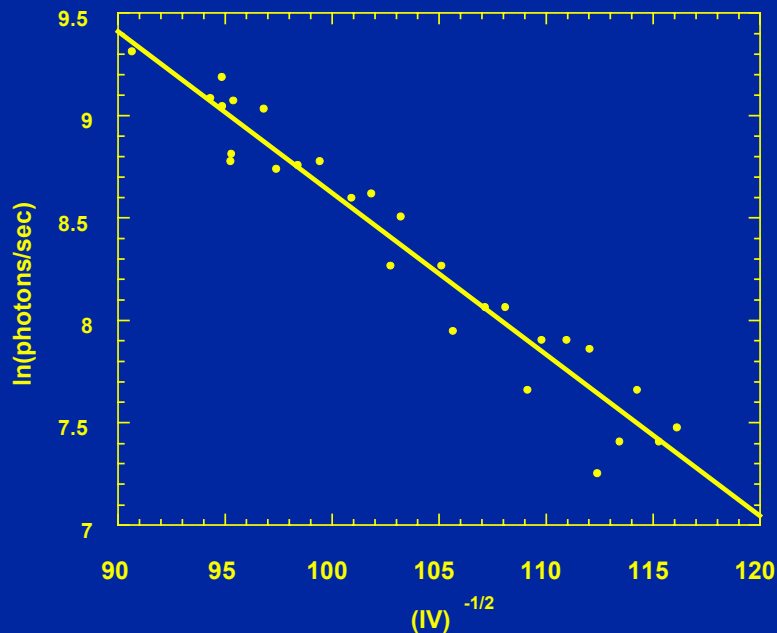
**Upper line: current**  
**dashed line: current relating  
to one quantum**  
**lower line: quantum efficiency**



**Thin line: photons per second  
detected**

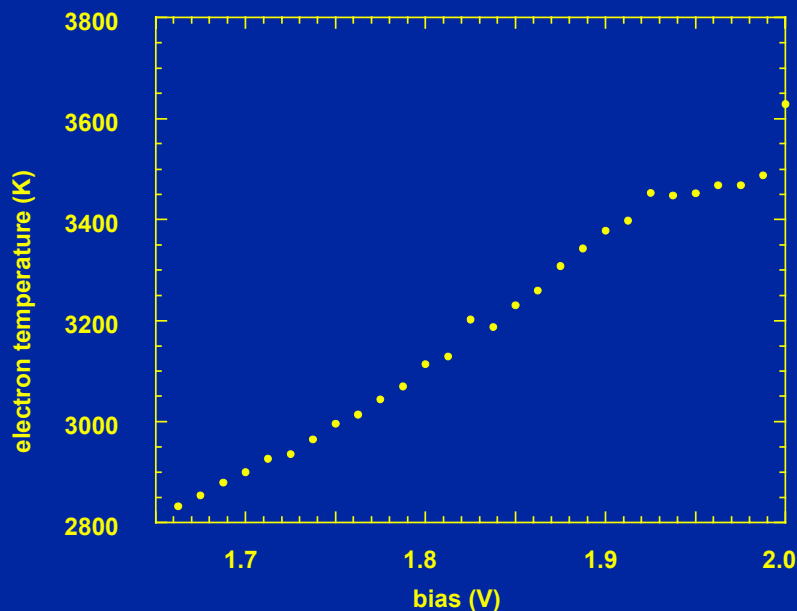
**thick line: electron temperature  
for  $\alpha = 4.8 \times 10^{-35}$  and  $h\nu = 2.1\text{eV}$ .**





**Now add a 2.4–2.6eV filter before PM tube.**

**Log plot of detected photons to determine the electron temperature. The range of counts per point is 12–94, and the slope is -0.079. Conductance of the contact ~0.4 quanta.**

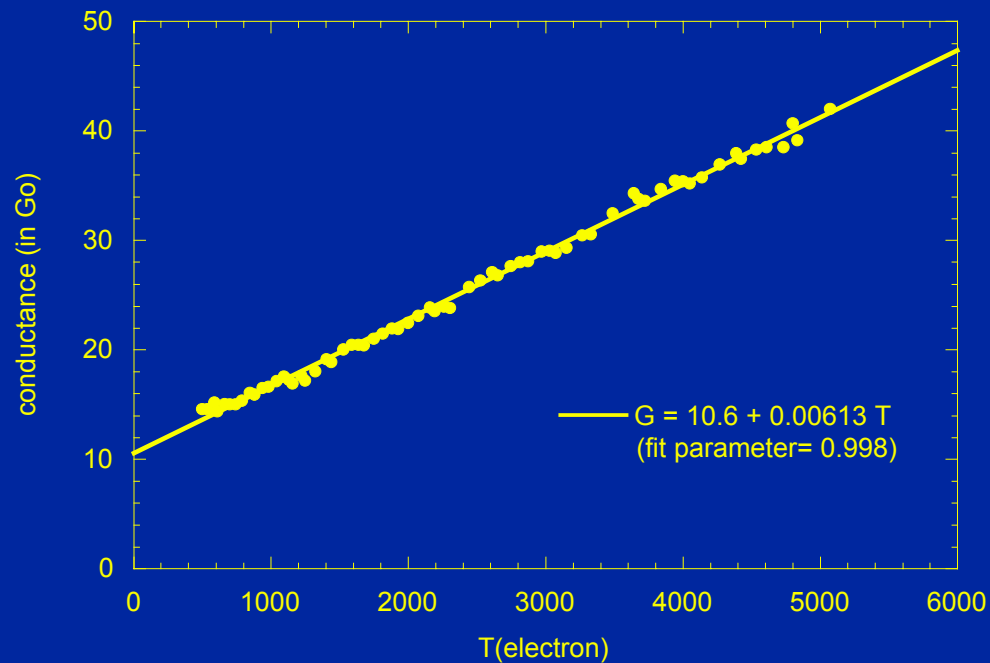
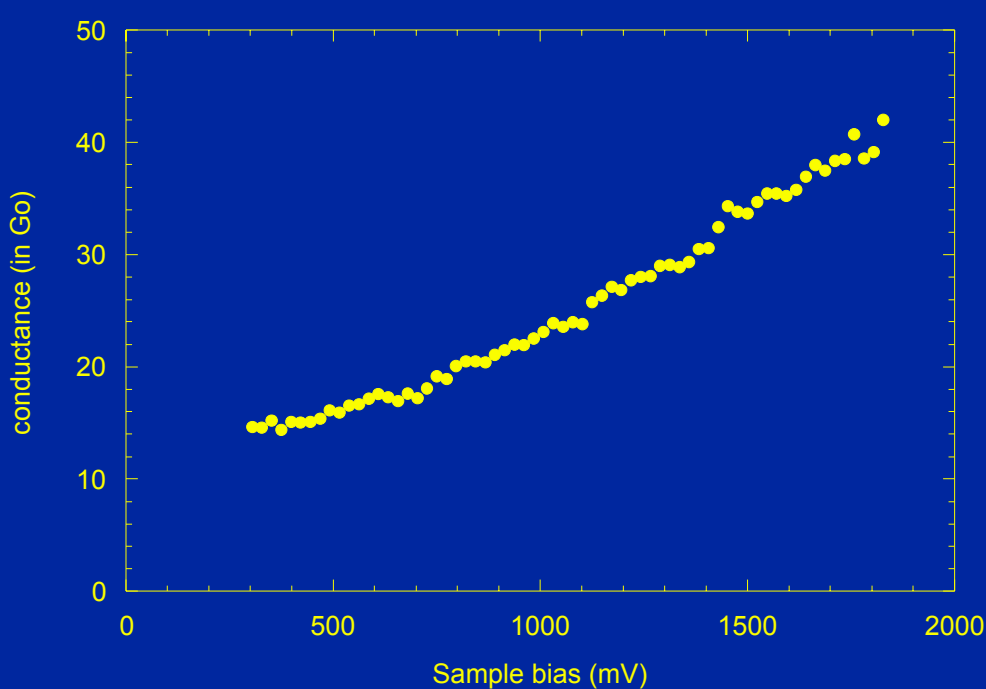


**Electron temperature plotted as a function of bias, using the relation**

$$kT_{\text{el}} = \sqrt{\alpha IV}$$

## Non-linear conductance

**For a contact of size  $\sim 10$  atoms, conductance increases with bias.**



**Relation between conductance and electron temperature is very linear.**

## High current densities

**Observe  $\sim 10^{15} \text{ Am}^{-2}$  in stable contacts. c.f.  $\sim 10^{12} \text{ Am}^{-2}$  necessary for macroscopic wires to fail. This higher stability is due to the lack of heat transfer between electrons and phonons in the contact.**

**This demonstrates that contacts below some critical size,  $L$  will have higher current-carrying capabilities**

## **Other potential mechanisms to be ruled out:**

- **ohmic heating –the electrons would be at a higher temperature than the melting temperature of the lattice.**

- **photon emission from the decay of some electron excitation –  
can be discounted because of the form of the  
emission spectrum found here,**

$$W(\nu) \sim \exp\left(\frac{-h\nu}{kT_{el}}\right)$$

- **plasmon-mediated photon emission from the STM –  
requires the emitted photon energy to be no higher  
than the electron energy, but here 2.5eV photons  
were emitted for a bias of 600mV.**

## **Conclusions**

- **High current densities in nanowires**
- **Wires/contacts  $\sim$ several nm in size stable at high current densities.**
- **For STM point contacts light emission consistent with high electron temperature.**
- **Divergence of electron and lattice temperature.**

# **Acknowledgements**

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